



# VN920PEP

## SINGLE CHANNEL HIGH SIDE SOLID STATE RELAY

### TARGET SPECIFICATION

TYPE	$R_{DS(on)}$	$I_{OUT}$	$V_{CC}$
VN920PEP	15m $\Omega$	30 A	36 V

- CMOS COMPATIBLE INPUT
- PROPORTIONAL LOAD CURRENT SENSE
- SHORTED LOAD PROTECTION
- UNDERVOLTAGE AND OVERVOLTAGE SHUTDOWN
- OVERVOLTAGE CLAMP
- THERMAL SHUTDOWN
- CURRENT LIMITATION
- PROTECTION AGAINST LOSS OF GROUND AND LOSS  $V_{CC}$
- VERY LOW STAND-BY POWER DISSIPATION
- REVERSE BATTERY PROTECTION (\*)

### DESCRIPTION

The VN920PEP is a monolithic device designed in STMicroelectronics VIPower M0-3 Technology, intended for driving any kind of load with one side connected to ground. Active  $V_{CC}$  pin voltage clamp protects the device against low energy

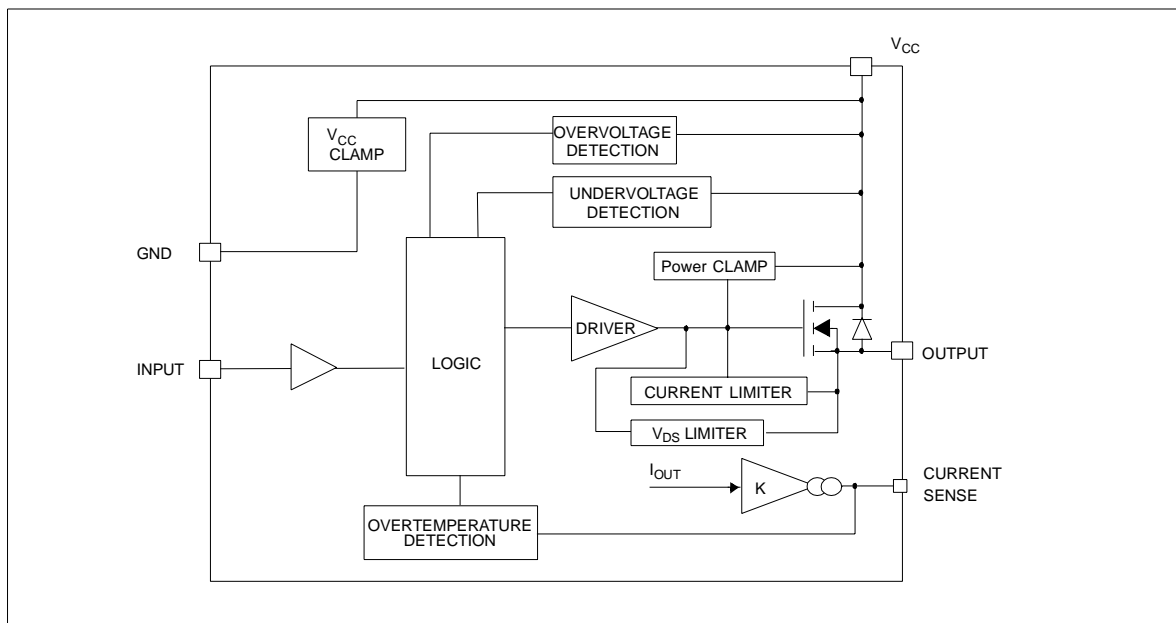


**PowerSSO-24**

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spikes (see ISO7637 transient compatibility table). Active current limitation combined with thermal shutdown and automatic restart protect the device against overload. The device integrates an analog current sense output which delivers a current proportional to the load current. Device automatically turns off in case of ground pin disconnection.

### BLOCK DIAGRAM



(\*) See application schematic at page 8

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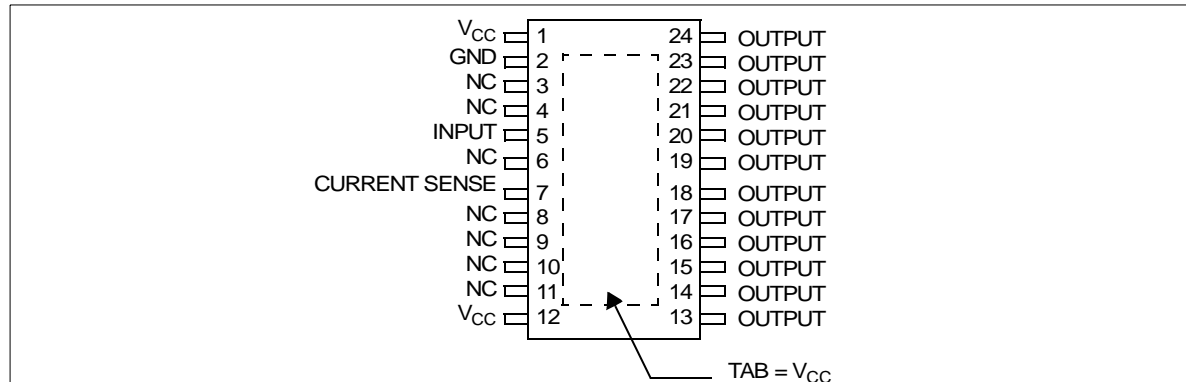
This is preliminary information on a new product foreseen to be developed. Details are subject to change without notice.

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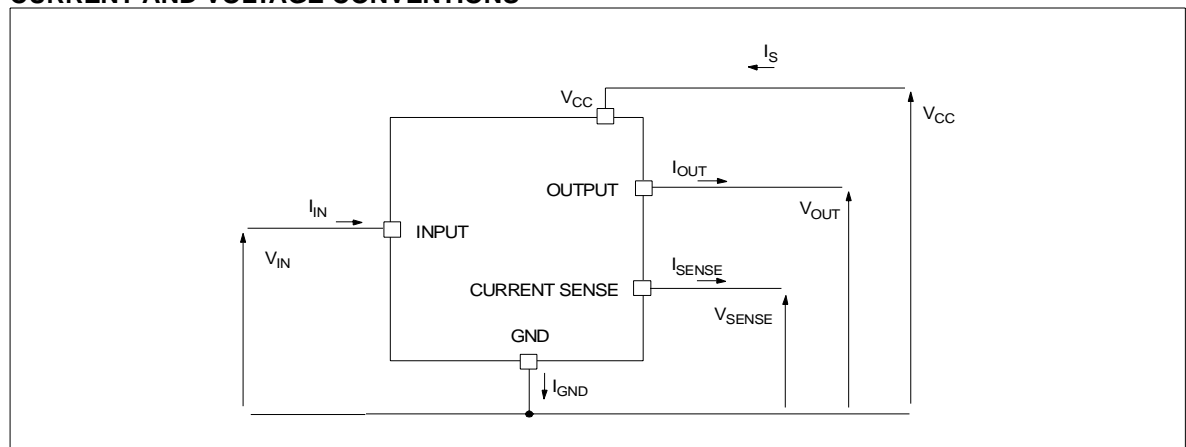
## ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
$V_{CC}$	DC Supply Voltage	41	V
$-V_{CC}$	Reverse DC Supply Voltage	- 0.3	V
$-I_{GND}$	DC Reverse Ground Pin Current	- 200	mA
$I_{OUT}$	DC Output Current	Internally Limited	A
$-I_{OUT}$	Reverse DC Output Current	- 40	A
$I_{IN}$	DC Input Current	+/- 10	mA
$V_{CSENSE}$	Current Sense Maximum Voltage	-3	V
		+15	V
$V_{ESD}$	Electrostatic Discharge (Human Body Model: R=1.5K $\Omega$ ; C=100pF)		
	- INPUT	4000	V
	- CURRENT SENSE	2000	V
	- OUTPUT	5000	V
	- $V_{CC}$	5000	V
$P_{tot}$	Power Dissipation $T_C \leq 25^\circ C$	96	W
$T_j$	Junction Operating Temperature	Internally limited	$^\circ C$
$T_C$	Case Operating Temperature	- 40 to 150	$^\circ C$
$T_{STG}$	Storage Temperature	- 55 to 150	$^\circ C$

## CONNECTION DIAGRAM (TOP VIEW)



## CURRENT AND VOLTAGE CONVENTIONS



## THERMAL DATA

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal Resistance Junction-case	Max	1.3 °C/W
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	60 (*) °C/W

(\*) When mounted on a standard single-sided FR-4 board with 1cm<sup>2</sup> of Cu (at least 35µm thick).

ELECTRICAL CHARACTERISTICS (8V < V<sub>CC</sub> < 36V; -40°C < T<sub>j</sub> < 150°C unless otherwise specified)

## POWER

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V <sub>CC</sub>	Operating Supply Voltage		5.5	13	36	V
V <sub>USD</sub>	Undervoltage Shut-down		3	4	5.5	V
V <sub>OV</sub>	Overvoltage Shut-down		36			V
R <sub>ON</sub>	On State Resistance	I <sub>OUT</sub> =10A; T <sub>j</sub> =25°C I <sub>OUT</sub> =10A I <sub>OUT</sub> =3A; V <sub>CC</sub> =6V			15 30 50	mΩ mΩ mΩ
V <sub>clamp</sub>	Clamp Voltage	I <sub>CC</sub> =20mA (See note 1)	41	48	55	V
I <sub>S</sub>	Supply Current	Off State; V <sub>CC</sub> =13V; V <sub>IN</sub> =V <sub>OUT</sub> =0V Off State; V <sub>CC</sub> =13V; T <sub>j</sub> =25°C; V <sub>IN</sub> =V <sub>OUT</sub> =0V On State; V <sub>CC</sub> =13V; V <sub>IN</sub> =5V; I <sub>OUT</sub> =0; R <sub>SENSE</sub> =3.9KΩ		10 10	25 20 5	µA µA mA
I <sub>L(off1)</sub>	Off State Output Current	V <sub>IN</sub> =V <sub>OUT</sub> =V <sub>SENSE</sub> =0V	0		50	µA
I <sub>L(off2)</sub>	Off State Output Current	V <sub>IN</sub> =V <sub>SENSE</sub> =0V; V <sub>OUT</sub> =3.5V	-75		0	µA
I <sub>L(off3)</sub>	Off State Output Current	V <sub>IN</sub> =V <sub>OUT</sub> =V <sub>SENSE</sub> =0V; V <sub>CC</sub> =13V; T <sub>j</sub> =125°C			5	µA
I <sub>L(off4)</sub>	Off State Output Current	V <sub>IN</sub> =V <sub>OUT</sub> =V <sub>SENSE</sub> =0V; V <sub>CC</sub> =13V; T <sub>j</sub> =25°C			3	µA

SWITCHING (V<sub>CC</sub>=13V)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
t <sub>d(on)</sub>	Turn-on Delay Time	R <sub>L</sub> =1.3Ω (see figure 2)		50		µs
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>L</sub> =1.3Ω (see figure 2)		50		µs
dV <sub>OUT</sub> /dt <sub>(on)</sub>	Turn-on Voltage Slope	R <sub>L</sub> =1.3Ω (see figure 2)		See relative diagram		V/µs
dV <sub>OUT</sub> /dt <sub>(off)</sub>	Turn-off Voltage Slope	R <sub>L</sub> =1.3Ω (see figure 2)		See relative diagram		V/µs

## LOGIC INPUT

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V <sub>IL</sub>	Input Low Level				1.25	V
I <sub>IL</sub>	Low Level Input Current	V <sub>IN</sub> =1.25V	1			µA
V <sub>IH</sub>	Input High Level		3.25			V
I <sub>IH</sub>	High Level Input Current	V <sub>IN</sub> =3.25V			10	µA
V <sub>I(hyst)</sub>	Input Hysteresis Voltage		0.5			V
V <sub>ICL</sub>	Input Clamp Voltage	I <sub>IN</sub> =1mA I <sub>IN</sub> =-1mA	6	6.8 -0.7	8	V V

Note 1: V<sub>clamp</sub> and V<sub>OV</sub> are correlated. Typical difference is 5V.

## VN920PEP

### ELECTRICAL CHARACTERISTICS (continued)

CURRENT SENSE ( $9V \leq V_{CC} \leq 16V$ ) (See Fig. 1)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$K_1$	$I_{OUT}/I_{SENSE}$	$I_{OUT}=1A; V_{SENSE}=0.5V;$ $T_j = -40^\circ C \dots 150^\circ C$	3300	4400	6000	
$dK_1/K_1$	Current Sense Ratio Drift	$I_{OUT}=1A; V_{SENSE}=0.5V;$ $T_j = -40^\circ C \dots +150^\circ C$	-10		+10	%
$K_2$	$I_{OUT}/I_{SENSE}$	$I_{OUT}=10A; V_{SENSE}=4V; T_j=-40^\circ C$ $T_j=25^\circ C \dots 150^\circ C$	4200 4400	4900 4900	6000 5750	
$dK_2/K_2$	Current Sense Ratio Drift	$I_{OUT}=10A; V_{SENSE}=4V;$ $T_j=-40^\circ C \dots +150^\circ C$	-8		+8	%
$K_3$	$I_{OUT}/I_{SENSE}$	$I_{OUT}=30A; V_{SENSE}=4V; T_j=-40^\circ C$ $T_j=25^\circ C \dots 150^\circ C$	4200 4400	4900 4900	5500 5250	
$dK_3/K_3$	Current Sense Ratio Drift	$I_{OUT}=30A; V_{SENSE}=4V;$ $T_j=-40^\circ C \dots +150^\circ C$	-6		+6	%
$I_{SENSE0}$	Analog Sense Leakage Current	$V_{CC}=6 \dots 16V; I_{OUT}=0A; V_{SENSE}=0V;$ $T_j=-40^\circ C \dots +150^\circ C$	0		10	$\mu A$
$V_{SENSE}$	Max Analog Sense Output Voltage	$V_{CC}=5.5V; I_{OUT}=5A; R_{SENSE}=10K\Omega$ $V_{CC}>8V; I_{OUT}=10A; R_{SENSE}=10K\Omega$	2 4			V V
$V_{SENSEH}$	Sense Voltage in Overtemperature conditions	$V_{CC}=13V; R_{SENSE}=3.9K\Omega$		5.5		V
$R_{VSENSEH}$	Analog sense output impedance in overtemperature condition	$V_{CC}=13V; T_j > T_{TSD};$ Output Open		400		$\Omega$
$t_{DSENSE}$	Current sense delay response	to 90% $I_{SENSE}$ (see note 2)			500	$\mu s$

### PROTECTIONS

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$T_{TSD}$	Shut-down Temperature		150	175	200	$^\circ C$
$T_R$	Reset Temperature		135			$^\circ C$
$T_{hyst}$	Thermal Hysteresis		7	15		$^\circ C$
$I_{lim}$	DC Short Circuit Current	$V_{CC}=13V$ $5V < V_{CC} < 36V$	30	45	75 75	A A
$V_{demag}$	Turn-off Output Clamp Voltage	$I_{OUT}=2A; V_{IN}=0V; L=6mH$	$V_{CC}-41$	$V_{CC}-48$	$V_{CC}-55$	V
$V_{ON}$	Output Voltage Drop Limitation	$I_{OUT}=1A; T_j=-40^\circ C \dots +150^\circ C$		50		mV

### VCC - OUTPUT DIODE

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_F$	Forward on Voltage	$-I_{OUT}=5.5A; T_j=150^\circ C$			0.7	V

Note 2: current sense signal delay after positive input slope

Note: Sense pin doesn't have to be left floating.

Figure 1:  $I_{OUT}/I_{SENSE}$  versus  $I_{OUT}$

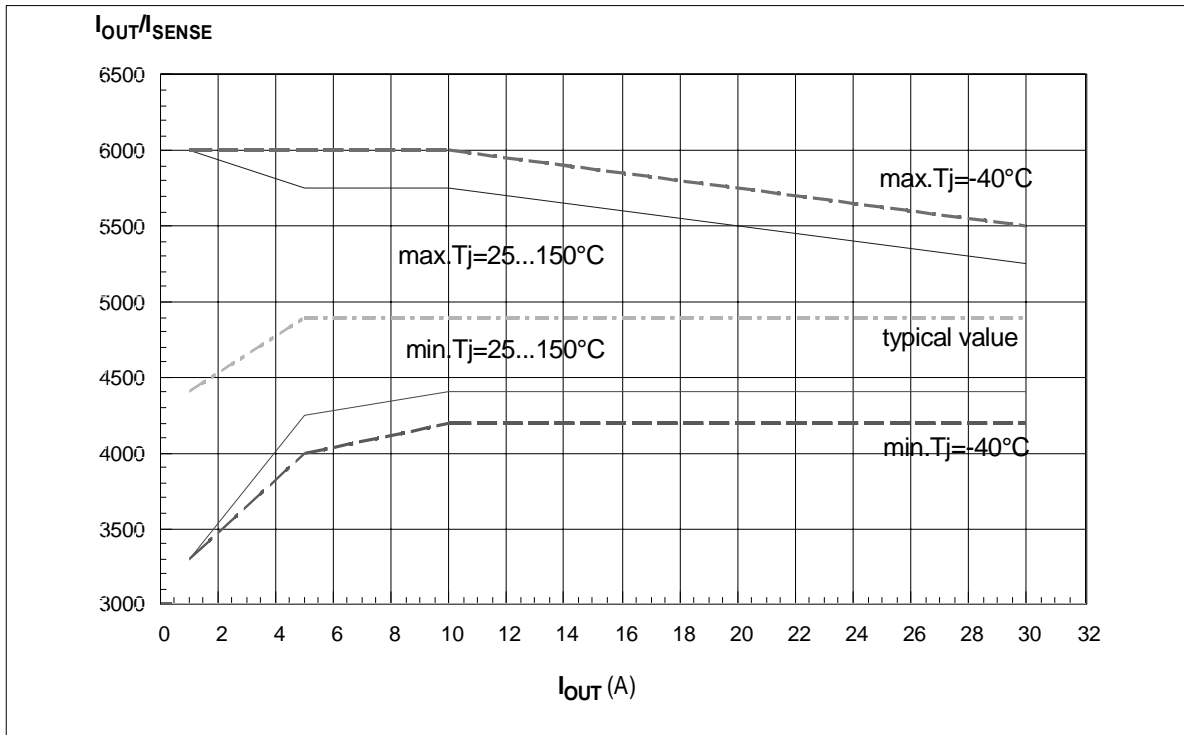
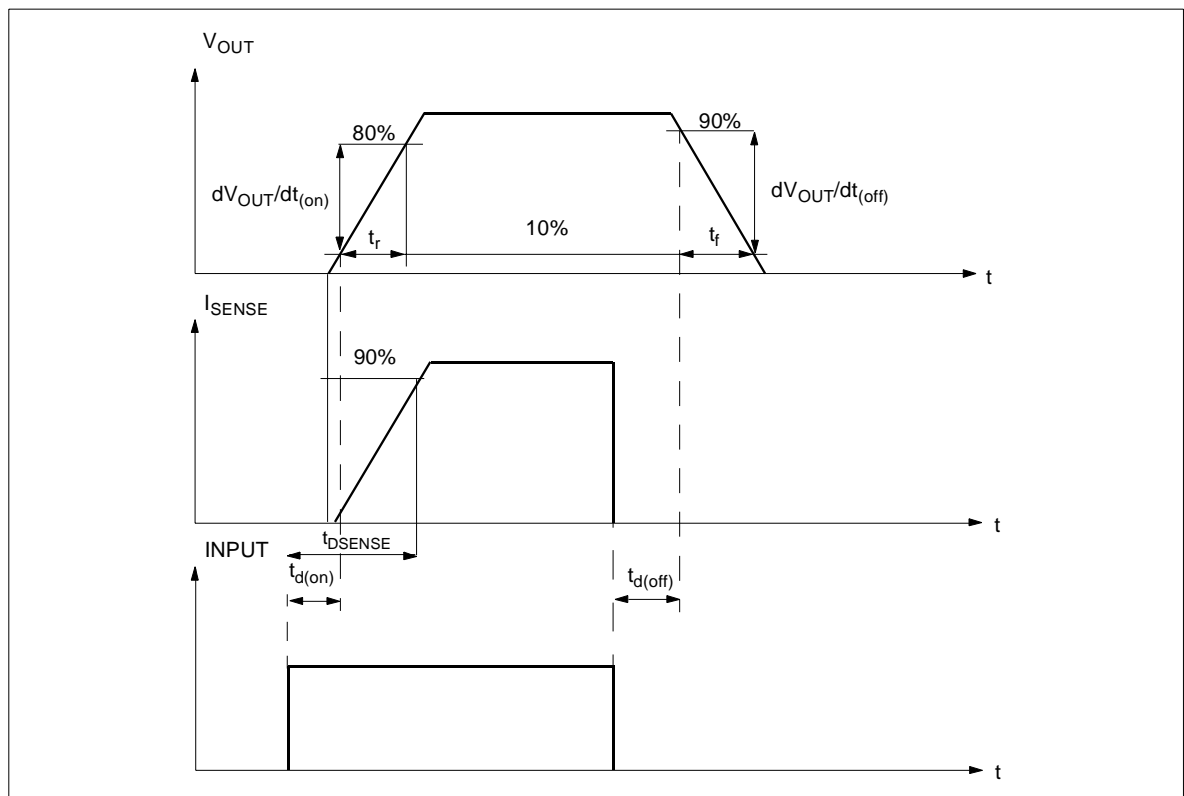


Figure 2: Switching Characteristics (Resistive load  $R_L = 1.3\Omega$ )



## VN920PEP

### TRUTH TABLE

CONDITIONS	INPUT	OUTPUT	SENSE
Normal operation	L	L	0
	H	H	Nominal
Overtemperature	L	L	0
	H	L	$V_{SENSEH}$
Undervoltage	L	L	0
	H	L	0
Overvoltage	L	L	0
	H	L	0
Short circuit to GND	L	L	0
	H	L	$(T_j < T_{TSD})$ 0
	H	L	$(T_j > T_{TSD})$ $V_{SENSEH}$
Short circuit to $V_{CC}$	L	H	0
	H	H	< Nominal
Negative output voltage clamp	L	L	0

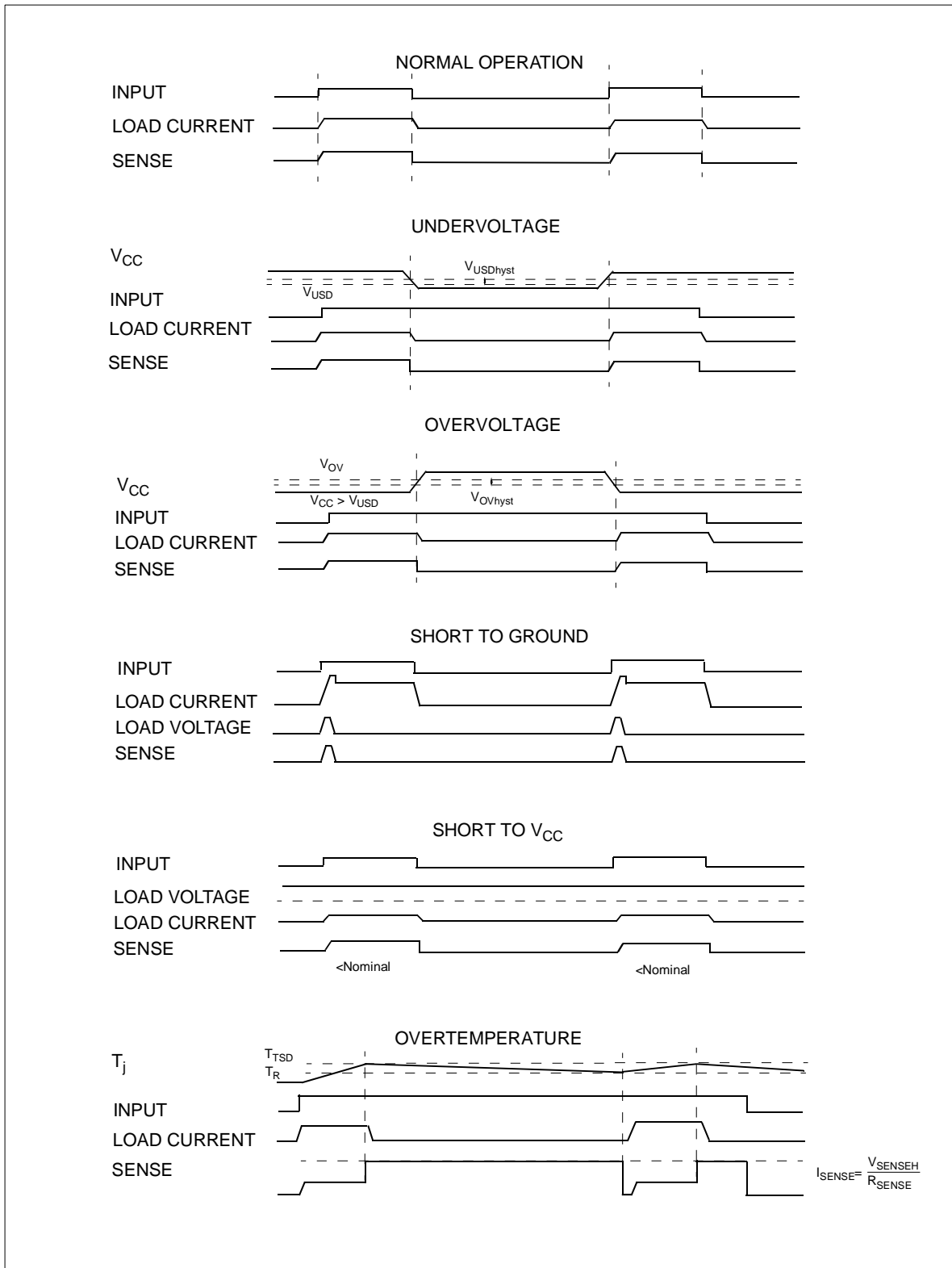
### ELECTRICAL TRANSIENT REQUIREMENTS

ISO T/R 7637/1 Test Pulse	TEST LEVELS				Delays and Impedance
	I	II	III	IV	
1	-25 V	-50 V	-75 V	-100 V	2 ms 10 $\Omega$
2	+25 V	+50 V	+75 V	+100 V	0.2 ms 10 $\Omega$
3a	-25 V	-50 V	-100 V	-150 V	0.1 $\mu$ s 50 $\Omega$
3b	+25 V	+50 V	+75 V	+100 V	0.1 $\mu$ s 50 $\Omega$
4	-4 V	-5 V	-6 V	-7 V	100 ms, 0.01 $\Omega$
5	+26.5 V	+46.5 V	+66.5 V	+86.5 V	400 ms, 2 $\Omega$

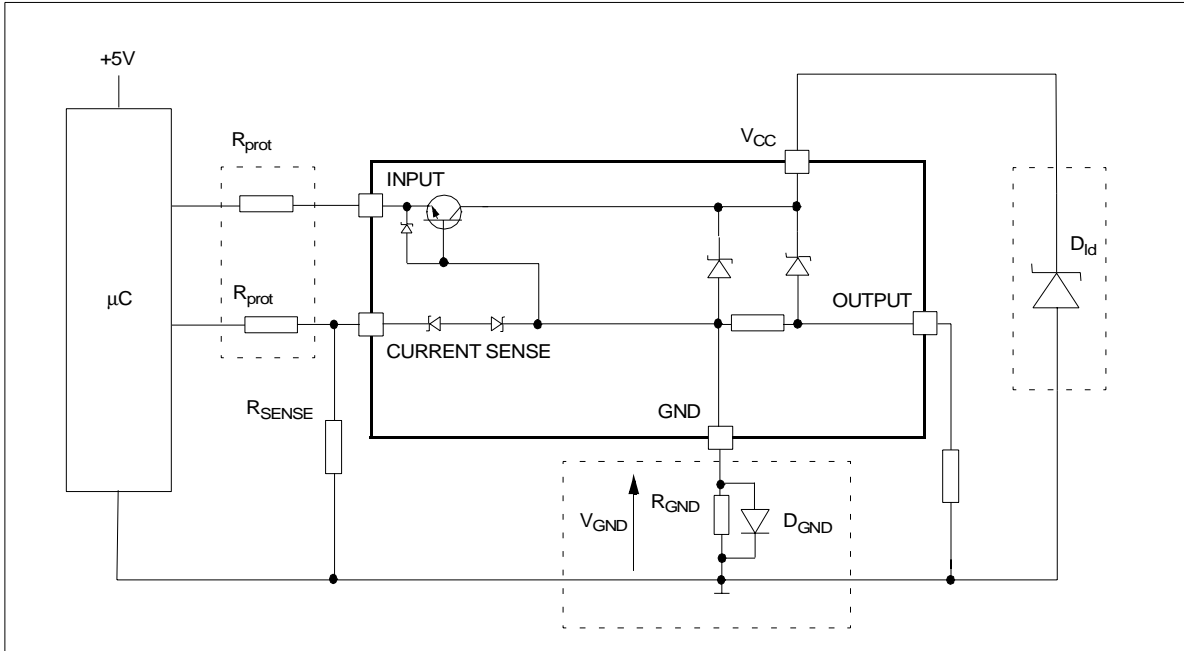
ISO T/R 7637/1 Test Pulse	TEST LEVELS RESULTS			
	I	II	III	IV
1	C	C	C	C
2	C	C	C	C
3a	C	C	C	C
3b	C	C	C	C
4	C	C	C	C
5	C	E	E	E

CLASS	CONTENTS
C	All functions of the device are performed as designed after exposure to disturbance.
E	One or more functions of the device is not performed as designed after exposure to disturbance and cannot be returned to proper operation without replacing the device.

Figure 3: Waveforms



APPLICATION SCHEMATIC



**GND PROTECTION NETWORK AGAINST REVERSE BATTERY**

**Solution 1:** Resistor in the ground line ( $R_{GND}$  only). This can be used with any type of load.

The following is an indication on how to dimension the  $R_{GND}$  resistor.

- 1)  $R_{GND} \leq 600\text{mV} / (I_{S(on)max})$ .
- 2)  $R_{GND} \geq (-V_{CC}) / (-I_{GND})$

where  $-I_{GND}$  is the DC reverse ground pin current and can be found in the absolute maximum rating section of the device's datasheet.

Power Dissipation in  $R_{GND}$  (when  $V_{CC} < 0$ : during reverse battery situations) is:

$$P_D = (-V_{CC})^2 / R_{GND}$$

This resistor can be shared amongst several different HSD. Please note that the value of this resistor should be calculated with formula (1) where  $I_{S(on)max}$  becomes the sum of the maximum on-state currents of the different devices.

Please note that if the microprocessor ground is not common with the device ground then the  $R_{GND}$  will produce a shift ( $I_{S(on)max} * R_{GND}$ ) in the input thresholds and the status output values. This shift will vary depending on how many devices are ON in the case of several high side drivers sharing the same  $R_{GND}$ .

If the calculated power dissipation leads to a large resistor or several devices have to share the same resistor then the ST suggests to utilize Solution 2 (see below).

**Solution 2:** A diode ( $D_{GND}$ ) in the ground line.

A resistor ( $R_{GND} = 1\text{k}\Omega$ ) should be inserted in parallel to  $D_{GND}$  if the device will be driving an inductive load.

This small signal diode can be safely shared amongst several different HSD. Also in this case, the presence of the ground network will produce a shift ( $\approx 600\text{mV}$ ) in the input threshold and the status output values if the microprocessor ground is not common with the device ground. This shift will not vary if more than one HSD shares the same diode/resistor network.

Series resistor in INPUT line is also required to prevent that, during battery voltage transient, the current exceeds the Absolute Maximum Rating.

Safest configuration for unused INPUT pin is to leave it unconnected, while unused SENSE pin has to be connected to Ground pin.

**LOAD DUMP PROTECTION**

$D_{Id}$  is necessary (Voltage Transient Suppressor) if the load dump peak voltage exceeds  $V_{CC}$  max DC rating. The same applies if the device will be subject to transients on the  $V_{CC}$  line that are greater than the ones shown in the ISO T/R 7637/1 table.

**µC I/Os PROTECTION:**

If a ground protection network is used and negative transients are present on the  $V_{CC}$  line, the control pins will be pulled negative. ST suggests to insert a resistor ( $R_{prot}$ ) in line to prevent the µC I/Os pins to latch-up.

The value of these resistors is a compromise between the leakage current of µC and the current required by the HSD I/Os (Input levels compatibility) with the latch-up limit of µC I/Os.

$$-V_{CCpeak} / I_{latchup} \leq R_{prot} \leq (V_{OH\mu C} - V_{IH} - V_{GND}) / I_{IHmax}$$

Calculation example:

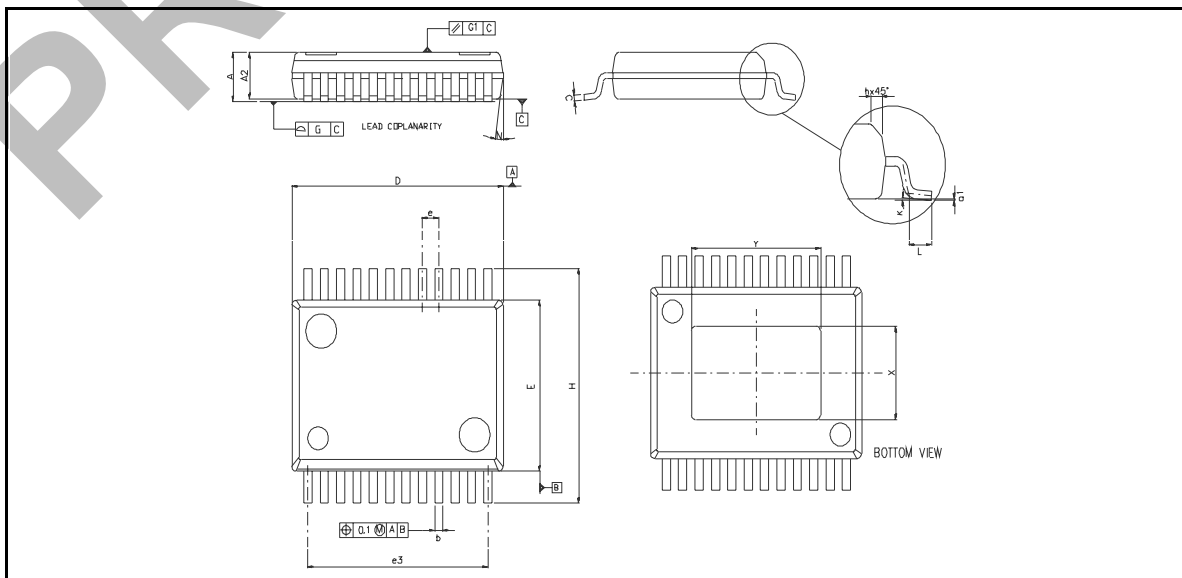
For  $V_{CCpeak} = -100\text{V}$  and  $I_{latchup} \geq 20\text{mA}$ ;  $V_{OH\mu C} \geq 4.5\text{V}$   
 $5\text{k}\Omega \leq R_{prot} \leq 65\text{k}\Omega$ .

Recommended  $R_{prot}$  value is  $10\text{k}\Omega$ .



## PowerSSO-24™ MECHANICAL DATA

DIM.	mm.		
	MIN.	TYP	MAX.
A	1.9		2.22
A2	1.9		2.15
a1	0		0.07
b	0.34	0.4	0.46
c	0.23		0.32
D	10.2		10.4
E	7.4		7.6
e		0.8	
e3		8.8	
G			0.1
G1			0.06
H	10.1		10.5
h			0.4
L	0.55		0.85
N			10°
X	3.9		4.3
Y	6.1		6.5



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